

Static Random Access Memory (SRAM) - Market Share Analysis, Industry Trends & Statistics, Growth Forecasts (2025 - 2030)

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Report description:

Static Random Access Memory (SRAM) Market Analysis

The global Static Random Access Memory market size stood at USD 1.71 billion in 2025 and is forecast to advance at a 5.60% CAGR to reach USD 2.25 billion by 2030. Growth reflected the transition toward AI-centric compute, 5G roll-outs, and real-time edge processing, all of which rely on SRAM's ultra-low latency for cache hierarchies. Semiconductor vendors prioritized shrinking SRAM cells at 2 nm to support larger L2/L3 caches while keeping power budgets in check. Data-center modernization drove demand for high-speed buffers in switches and accelerators, whereas consumer device refresh cycles maintained a steady baseline. Supply-chain resilience became pivotal after the 2024 Taiwan earthquake disrupted foundry output, prompting geographic diversification initiatives. Meanwhile, emerging non-volatile memories such as MRAM intensified competitive pressure on conventional SRAM in battery-backed designs.

Global Static Random Access Memory (SRAM) Market Trends and Insights

Rising demand for faster cache memories

Advanced CPUs and GPUs shipped in 2025 featured larger on-chip caches to cut inference latency, with Intel's Xeon 6 showing a 1.4x performance lift tied to cache optimization. TSMC's 2 nm platform delivered higher SRAM cell density than competing 18A nodes, giving hyperscale customers more L3 cache per watt. Marvell unveiled 2 nm custom SRAM that packs 6 Gb of low-power memory, reducing energy use by 66% versus prior nodes. Such innovations enabled AI accelerators to keep model parameters

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closer to compute units, sustaining throughput while containing DRAM traffic. Consequently, the Static Random Access Memory market benefited from recurring capacity upgrades across data-center and edge silicon.

Data-center and 5G network build-out

Cloud operators doubled rack densities to host AI servers, prompting wider use of SRAM-based packet buffers in top-of-rack switches. Microsoft tested 246-275 GHz wireless backplanes in server halls, where microsecond-scale buffering relied on high-speed SRAM. Cisco's converged 5G transport promoted deterministic latency, necessitating deep SRAM queues in routers. Corning forecasts an 18% jump in fiber demand per AI rack, mirroring the scaling of switch buffers built on synchronous SRAM. This infrastructure wave reinforced near-term revenue visibility for the Static Random Access Memory market.

High cost per bit vs. DRAM/NAND

SRAM remained several times more expensive per bit than commodity DRAM, pressuring designers to trim usage in mass-market gadgets. DDR4 module prices climbed roughly 50% in H1 2025, illustrating volatility across the memory stack. Samsung leveraged tightening supply to lift LPDDR4 pricing, but that tactic risked accelerating OEM interest in hybrid SRAM-DRAM architectures to curb bills of materials. Consequently, the Static Random Access Memory market faced pushback in entry-level consumer segments until density-versus-cost trade-offs improved.

Other drivers and restraints analyzed in the detailed report include:

IoT and wearable device proliferation / In-memory AI accelerators adoption / Emerging NVM (MRAM/ReRAM) displacement /

For complete list of drivers and restraints, kindly check the Table Of Contents.

Segment Analysis

Synchronous SRAM captured 58.4% Static Random Access Memory market share in 2024, underscoring its indispensability for deterministic cache operation in CPUs, GPUs, and network ASICs. Automotive MCUs used synchronous arrays to meet stringent real-time requirements for driver-assistance workloads. The segment will maintain leadership as advanced nodes extend frequency envelopes and reduce core voltages.

Asynchronous SRAM expanded at a 6.4% CAGR and increasingly served IoT wearables and edge gateways where power budgets override latency targets. Energy-efficient designs eliminated clock trees and simplified board layouts, a boon for battery-operated healthcare devices employing Syntiant's neural coprocessors. This divergence emphasized the Static Random Access Memory market trend toward application-specific optimization rather than one-size-fits-all performance chasing.

Pseudo-SRAM held a 54.4% share in 2024 by embedding DRAM cells behind an SRAM-style interface, achieving higher density without refresh management at the system level. RAAAM Memory Technologies and NXP claimed 50% area and 10% power savings versus classic high-density SRAM, appealing to mass-market microcontrollers.

Non-volatile SRAM grew fastest at 8.7% CAGR as factories and vehicles demanded data integrity during brownouts. Industrial automation players selected nvSRAM modules to protect process variables, avoiding costly downtime. Although niche, this cohort enriched the Static Random Access Memory market landscape with value-added resilience features.

Static Random Access Memory (SRAM) Market is Segmented by Function (Asynchronous SRAM, and Synchronous SRAM), Product Type (Pseudo SRAM, Non-Volatile SRAM, and Other Product Types), Memory Density (8 Mb, 8-64 Mb, 64-256 Mb, and >256 Mb),

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End User (Consumer Electronics, Industrial, Communication Infrastructure, and More), and Geography (North America, South America, Europe, Asia-Pacific, and Middle East and Africa).

Geography Analysis

Asia-Pacific retained 61.4% Static Random Access Memory market share in 2024, fueled by Taiwan's foundry dominance, South Korea's memory innovation, and China's scale-up efforts. SK Hynix's rise to 36% of global DRAM output highlighted the region's technology depth. Yet the 2024 Taiwan quake exposed concentration risk, prompting contingency fabs in Japan and Singapore. Japan projected semiconductor equipment sales of JPY 5.51 trillion (USD 38.35 billion) in FY26, underscoring continued capacity build-out.

Middle East and Africa charted the fastest 7.5% CAGR, anchored by sovereign-fund spending to position the Gulf as a tri-continent data hub. Warehouse automation in the region was set for 17.5% annual growth to USD 1.6 billion by 2025, driving demand for reliable on-board caches. Africa's energy projects earmarked USD 730 billion in new capex to 2030, requiring industrial control systems that lean on SRAM for deterministic response.

North America focused on AI datacenter roll-outs, while Europe doubled down on sovereignty through the EUR 43 billion Chips Act. STMicroelectronics secured EUR 5 billion (USD 5.4 billion) for a Silicon Carbide campus in Italy, widening regional competency in power electronics that also consume specialized SRAM. Talent shortages, however, threatened expansion, with ASML warning it might shift operations if immigration tightened. These contrasts highlight diverse regional levers shaping the Static Random Access Memory market.

List of Companies Covered in this Report:

GSI Technology Inc. / Cypress Semiconductor Corp. (Infineon) / Renesas Electronics Corp. / Integrated Silicon Solution Inc. / Alliance Memory Inc. / Everspin Technologies Inc. / Samsung Electronics Co., Ltd. / Toshiba Electronic Devices & Storage Corp. / STMicroelectronics N.V. / SK hynix Inc. / Micron Technology Inc. / Nanya Technology Corp. / Winbond Electronics Corp. / Elite Semiconductor Memory Technology Inc. / Chiplus Semiconductor Corp. / Powerchip Semiconductor Mfg. Corp. / Puya Semiconductor Technology Co., Ltd. / Lyontek Inc. / ON Semiconductor Corporation / Texas Instruments Incorporated / Integrated Device Technology Inc. / NXP Semiconductors N.V. / Etron Technology Inc. / Espressif Systems (Shanghai) Co., Ltd. / SKYHigh Memory Ltd. /

Additional Benefits:

The market estimate (ME) sheet in Excel format /
3 months of analyst support /

Table of Contents:

1 INTRODUCTION

1.1 Study Assumptions and Market Definition

1.2 Scope of the Study

2 RESEARCH METHODOLOGY

3 EXECUTIVE SUMMARY

4 MARKET LANDSCAPE

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- 4.1 Market Overview
- 4.2 Market Drivers
 - 4.2.1 Rising demand for faster cache memories
 - 4.2.2 Data-center and 5G network build-out
 - 4.2.3 IoT and wearable device proliferation
 - 4.2.4 3D-integrated SRAM for chiplets
 - 4.2.5 Radiation-hardened SRAM for LEO satellites
 - 4.2.6 In-memory AI accelerators adoption
- 4.3 Market Restraints
 - 4.3.1 High cost per bit vs. DRAM/NAND
 - 4.3.2 Escalating power at 75 nm nodes
 - 4.3.3 Emerging NVM (MRAM/ReRAM) displacement
 - 4.3.4 Yield loss from lithography variability
- 4.4 Value Chain Analysis
- 4.5 Regulatory Landscape
- 4.6 Technological Outlook
- 4.7 Porter's Five Forces Analysis
 - 4.7.1 Threat of New Entrants
 - 4.7.2 Bargaining Power of Buyers
 - 4.7.3 Bargaining Power of Suppliers
 - 4.7.4 Threat of Substitutes
 - 4.7.5 Intensity of Rivalry
- 4.8 Impact of Macroeconomic Factors

5 MARKET SIZE AND GROWTH FORECASTS (VALUE)

- 5.1 By Function
 - 5.1.1 Asynchronous SRAM
 - 5.1.2 Synchronous SRAM
- 5.2 By Product Type
 - 5.2.1 Pseudo SRAM (PSRAM)
 - 5.2.2 Non-Volatile SRAM (nvSRAM)
 - 5.2.3 Other Product Types
- 5.3 By Memory Density
 - 5.3.1 8 Mb
 - 5.3.2 8 - 64 Mb
 - 5.3.3 64 - 256 Mb
 - 5.3.4 >256 Mb
- 5.4 By End User
 - 5.4.1 Consumer Electronics
 - 5.4.2 Industrial
 - 5.4.3 Communication Infrastructure
 - 5.4.4 Automotive and Aerospace
 - 5.4.5 Other End Users
- 5.5 By Geography
 - 5.5.1 North America
 - 5.5.1.1 United States
 - 5.5.1.2 Canada

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- 5.5.1.3 Mexico
- 5.5.2 South America
 - 5.5.2.1 Brazil
 - 5.5.2.2 Argentina
 - 5.5.2.3 Rest of South America
- 5.5.3 Europe
 - 5.5.3.1 Germany
 - 5.5.3.2 United Kingdom
 - 5.5.3.3 France
 - 5.5.3.4 Italy
 - 5.5.3.5 Russia
 - 5.5.3.6 Rest of Europe
- 5.5.4 Asia-Pacific
 - 5.5.4.1 China
 - 5.5.4.2 Japan
 - 5.5.4.3 South Korea
 - 5.5.4.4 India
 - 5.5.4.5 Taiwan
 - 5.5.4.6 Rest of Asia-Pacific
- 5.5.5 Middle East and Africa
 - 5.5.5.1 Middle East
 - 5.5.5.1.1 Turkey
 - 5.5.5.1.2 Israel
 - 5.5.5.1.3 GCC Countries
 - 5.5.5.1.4 Rest of Middle East
 - 5.5.5.2 Africa
 - 5.5.5.2.1 South Africa
 - 5.5.5.2.2 Nigeria
 - 5.5.5.2.3 Rest of Africa

6 COMPETITIVE LANDSCAPE

- 6.1 Market Concentration
- 6.2 Strategic Moves
- 6.3 Market Share Analysis
- 6.4 Company Profiles (includes Global level Overview, Market level overview, Core Segments, Financials as available, Strategic Information, Market Rank/Share for key companies, Products and Services, and Recent Developments)
 - 6.4.1 GSI Technology Inc.
 - 6.4.2 Cypress Semiconductor Corp. (Infineon)
 - 6.4.3 Renesas Electronics Corp.
 - 6.4.4 Integrated Silicon Solution Inc.
 - 6.4.5 Alliance Memory Inc.
 - 6.4.6 Everspin Technologies Inc.
 - 6.4.7 Samsung Electronics Co., Ltd.
 - 6.4.8 Toshiba Electronic Devices & Storage Corp.
 - 6.4.9 STMicroelectronics N.V.
 - 6.4.10 SK hynix Inc.
 - 6.4.11 Micron Technology Inc.

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- 6.4.12 Nanya Technology Corp.
- 6.4.13 Winbond Electronics Corp.
- 6.4.14 Elite Semiconductor Memory Technology Inc.
- 6.4.15 Chiplus Semiconductor Corp.
- 6.4.16 Powerchip Semiconductor Mfg. Corp.
- 6.4.17 Puya Semiconductor Technology Co., Ltd.
- 6.4.18 Lyontek Inc.
- 6.4.19 ON Semiconductor Corporation
- 6.4.20 Texas Instruments Incorporated
- 6.4.21 Integrated Device Technology Inc.
- 6.4.22 NXP Semiconductors N.V.
- 6.4.23 Etron Technology Inc.
- 6.4.24 Espressif Systems (Shanghai) Co., Ltd.
- 6.4.25 SKYHigh Memory Ltd.

7 MARKET OPPORTUNITIES AND FUTURE OUTLOOK

7.1 White-space and Unmet-need Assessment

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